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Abstract of the Disclosure

A light emitting device employing gallium nitride type compound semiconductor which generates no crystal defect, dislocation and can be separated easily to chips by cleavage and a method for producing the same are provided. As a substrate on which gallium nitride type compound semiconductor layers are stacked, a gallium nitride type compound semiconductor substrate, a single-crystal silicon, a group II-VI compound semiconductor substrate, or a group III-V compound semiconductor substrate is employed.